L Number	Hits	Search Text	DB	Time stamp
1	55	156/345.13.ccls.	USPAT	2004/01/07 10:48
2	890	((dress$3 clean$3 condition$3) with (pad cloth)) same (CMP "chemical mechanical")	USPAT	2004/01/07 12:56
3	114	(((dress$3 clean$3 condition$3) with (pad cloth)) same (CMP "chemical mechanical")) and ((analy$3 monitor$3 test$3) with (condition$3 dress$3 clean$3))	USPAT	2004/01/07 12:57
-	274	156/345.12 156/345.13 156/345.16	USPAT	2003/09/04 10:29
-	13915	(polishing planariz$5) same (grind$3 condition$3)	USPAT	2003/09/04 10:30
-	1270	("chemical mechanical" adj(polishing planariz$5) same (grind$3 condition$3))	USPAT	2003/09/04 10:32
-	0	(("chemical mechanical" adj(polishing planariz$5) same (grind$3 condition$3))) same ((analyz$3 monitor$3) adj3 (slurry solution))	USPAT	2003/09/04 10:34
-	10	(("chemical mechanical" adj(polishing planariz$5) same (grind$3 condition$3))) same ((analyz$3 monitor$3) same (slurry solution))	USPAT	2003/09/04 10:42
-	3517	("ammonium citrate" "nitric acid") same (cu copper)	USPAT	2003/09/04 10:48
-	559	(("ammonium citrate" "nitric acid") same (cu copper)) and (polish$3 abrad$3 planariz$5)	USPAT	2003/09/04 10:49
-	53	chopra-dinesh.in. meikle-scott.in.	USPAT	2003/09/04 12:59
-	1111	micron.as. and (condition$3 dress$3) and (analy$4 monitor$3)	USPAT	2003/09/04 13:00
-	261	micron.as. and (condition$3 dress$3) same (analy$4 monitor$3)	USPAT	2003/09/04 14:10
-	305	(polish$3 abrad$3) same (gas air) same (spring)	USPAT	2003/09/04 14:12
-	2	("chemical mechanical" adj (polish$3 abrad$3)) same (gas air) same (spring)	USPAT	2003/09/04 14:32
-	2422	("chemical mechanical" adj (polish$3 abrad$3)) same (dry plasma)	USPAT	2003/09/04 14:17
-	70	(("chemical mechanical" adj (polish$3 abrad$3)) same (dry plasma)) and (spring or "pressure releasing")	USPAT	2003/09/04 14:17
-	3598	((dry plasma) same (polish$3 abrad$3 planari$5))	EPO; JPO; DERWENT	2003/09/04 14:33
-	654	((dry plasma) adj5 (polish$3 abrad$3 planari$5))	EPO; JPO; DERWENT	2003/09/04 14:33
-	143	(((dry plasma) adj5 (polish$3 abrad$3 planari$5))) and (wafer semiconductor)	EPO; JPO; DERWENT	2003/09/04 14:50
-	11	(((dry plasma) adj5 (polish$3 abrad$3 planari$5))) and (wafer semiconductor) and (spring pressure)	USPAT; EPO; JPO; DERWENT	2003/09/04 14:51
-	1138	134/113 134/104.1	USPAT	2003/09/05 14:41
-	21	(134/113 134/104.1) and (dress$3 grind$3 condition$3 clean$3) near5 (pad cloth platen)	USPAT	2003/09/05 14:41